

DATA SHEET

THYRISTOR SURGE SUPPRESSORS MODEMS/LINE CARD

P61089B series

RoHS compliant & Halogen free



Product specification— December 18, 2018 V.0



Thyristor Surge Suppressors (TSS) Data Sheet

General Description

This device has been especially designed to protect 2 new high voltage, as well as classical SLICs, against transient overvoltages.

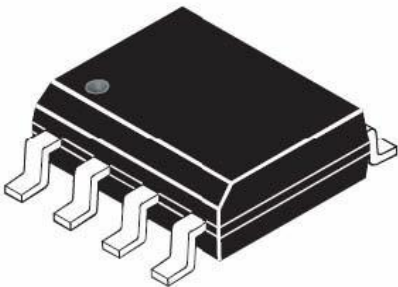
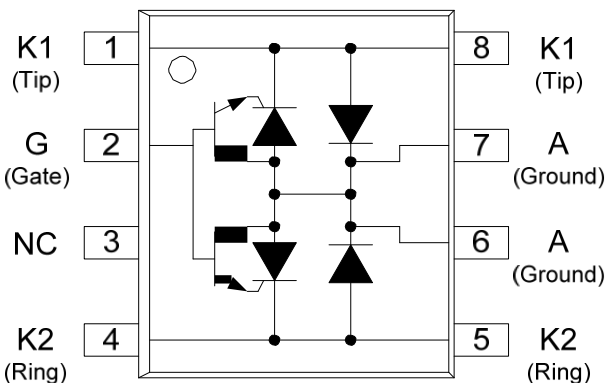
Positive overvoltages are clamped by 2 diodes. Negative surges are suppressed by 2 thyristors, their breakdown voltage being referenced to $-V_{BAT}$ through the gate.

This component presents a very low gate triggering current (I_{GT}) in order to reduce the current consumption on printed circuit board during the firing phase.

This devices are not subject to ageing and provide a fail safe mode in short circuit for a better protection. They are used to help equipment to meet various standards such as UL1950, IEC950/CSA C22.2, UL1459 and FCC part68.

Features

- Dual line programmable transient voltage suppressor
- Wide negative firing voltage range: $V_{MGL} = -155V$
- Holding current: $I_H > 150mA$
- Marking: H61089B
- Low dynamic switching voltages: V_{FP} and V_{DGL}
- Low gate triggering current: $I_{GT} = 5mA$ max
- Halogen Free

Package	Device Symbol
 SOP-8	

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage, $V_{GK}=0$	V_{DRM}	-170	V
Repetitive peak gate-cathode voltage, $V_{KA}=0$	V_{GKRM}	-170	V
Non-repetitive peak on-state current 10/1000 μs (Telcordia (Bellcore) GR-1089-CORE.Issue 2.February 1999, Section4) 5/320 μs (ITU-T K.20, K.21 & K.45, K.44 open-circuit voltage wave shape 10/700 μs) 1.2/50 μs (Telcordia (Bellcore) GR-1089-CORE.Issue 2.February 1999, Section4) 2/10 μs (Telcordia (Bellcore) GR-1089-CORE.Issue 2.February 1999, Section4)	I_{PPSM}	30 40 100 120	A
Non-repetitive peak on-state current. $V_{GG}=-75\text{V}$ 50Hz to 60Hz 0.1s 1s 5s 300s 900s	I_{TSM}	11 4.8 2.7 0.95 0.93	A
Operating free-air temperature range	T_A	-40 to +85	$^\circ\text{C}$
Operating junction temperature range	T_J	-40 to +150	$^\circ\text{C}$
Storage temperature range	T_{STG}	-40 to +150	$^\circ\text{C}$
Lead soldering temperature, 10 seconds	T_{LS}	300(Mix.)	$^\circ\text{C}$

Thermal Characteristics

Parameter	Test Conditions	Max	Unit
$R_{\theta JA}$ Junction to free air thermal temperature	$T_A = 25^\circ\text{C}$, EIA/JESD51-3 PCB, EIA/JESD51-2 environment, $P_{TOT} = 1.7\text{W}$	120	$^\circ\text{C/W}$

Parameter Measurement Information

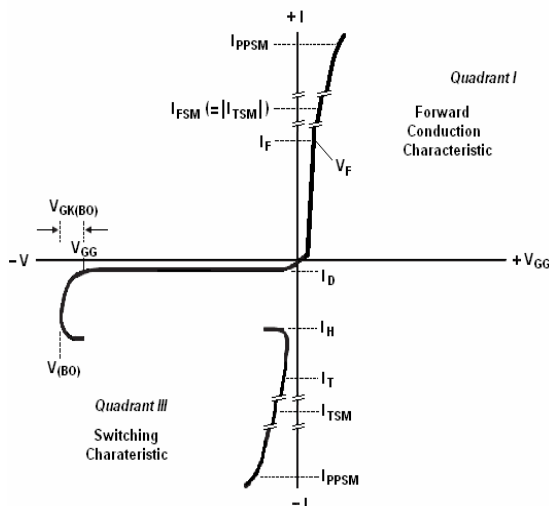


Figure 1. Voltage-Current Characteristic
Unless otherwise noted, all voltages are referenced to the anode

Electrical Characteristics, Rating at 25 °C unless otherwise specified

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_D	Off-state current $V_D = V_{DRM}$, $V_{GK} = 0$, $V_{G2} \geq +5V$ $T_J = 25^\circ C$ $T_J = 85^\circ C$			-5 -50	μA
$V_{(BO)}$	Breakover voltage $2/10\mu s$, $I_{PP} = -56A$, $R_S = 45\Omega$, $V_{GG} = -48V$, $C_G = 220nF$ $1.2/50\mu s$, $I_{PP} = -53A$, $R_S = 47\Omega$, $V_{GG} = -48V$, $C_G = 220nF$		-57 -60		V
$V_{GK(BO)}$	Gate-cathode impulse breakover voltage $2/10\mu s$, $I_{PP} = -56A$, $R_S = 45\Omega$, $V_{GG} = -48V$, $C_G = 220nF$ $1.2/50\mu s$, $I_{PP} = -53A$, $R_S = 47\Omega$, $V_{GG} = -48V$, $C_G = 220nF$		9 12	20	V
V_F	Forward voltage $I_F = 5A$, $T_W = 200\mu s$			3	V
V_{FRM}	Peak forward recovery voltage $2/10\mu s$, $I_{PP} = -56A$, $R_S = 45\Omega$, $V_{GG} = -48V$, $C_G = 220nF$ $1.2/50\mu s$, $I_{PP} = -53A$, $R_S = 47\Omega$, $V_{GG} = -48V$, $C_G = 220nF$		6 8		V
I_H	Holding current $I_T = -1A$, $di/dt = 1A/ms$, $V_{GG} = -48V$	-150			mA
I_{GKS}	Gate reverse current $V_{GG} = V_{GK} = V_{GKRM}$, $V_{KA} = 0$ $T_J = 25^\circ C$ $T_J = 85^\circ C$			-5 -50	μA
I_{GT}	Gate trigger current $I_T = -3A$, $t_{p(g)} \geq 20\mu s$, $V_{GG} = -48V$			5	mA
V_{GT}	Gate-cathode trigger voltage $I_T = -3A$, $t_{p(g)} \geq 20\mu s$, $V_{GG} = -48V$		2.5	4	V
Q_{GS}	Gate switching charge $1.2/50\mu s$, $I_{PP} = -53A$, $R_S = 47\Omega$, $V_{GG} = -48V$, $C_G = 220nF$		0.1		μC
C_{KA}	Cathode-anode off- state capacitance $F = 1MHz$, $V_D = 1V$, $I_G = 0$ $V_D = -3V$ $V_D = -48V$			100 50	pF

Typical Characteristics

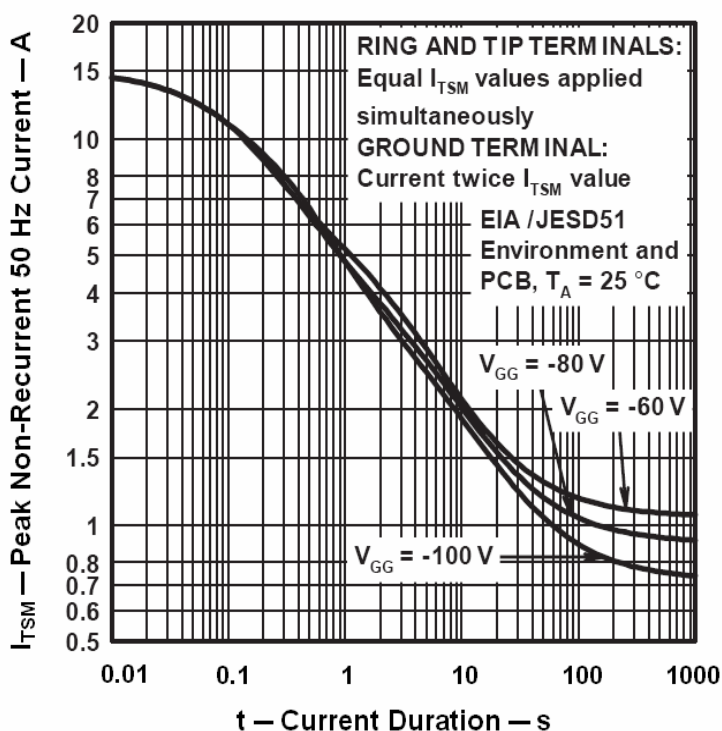
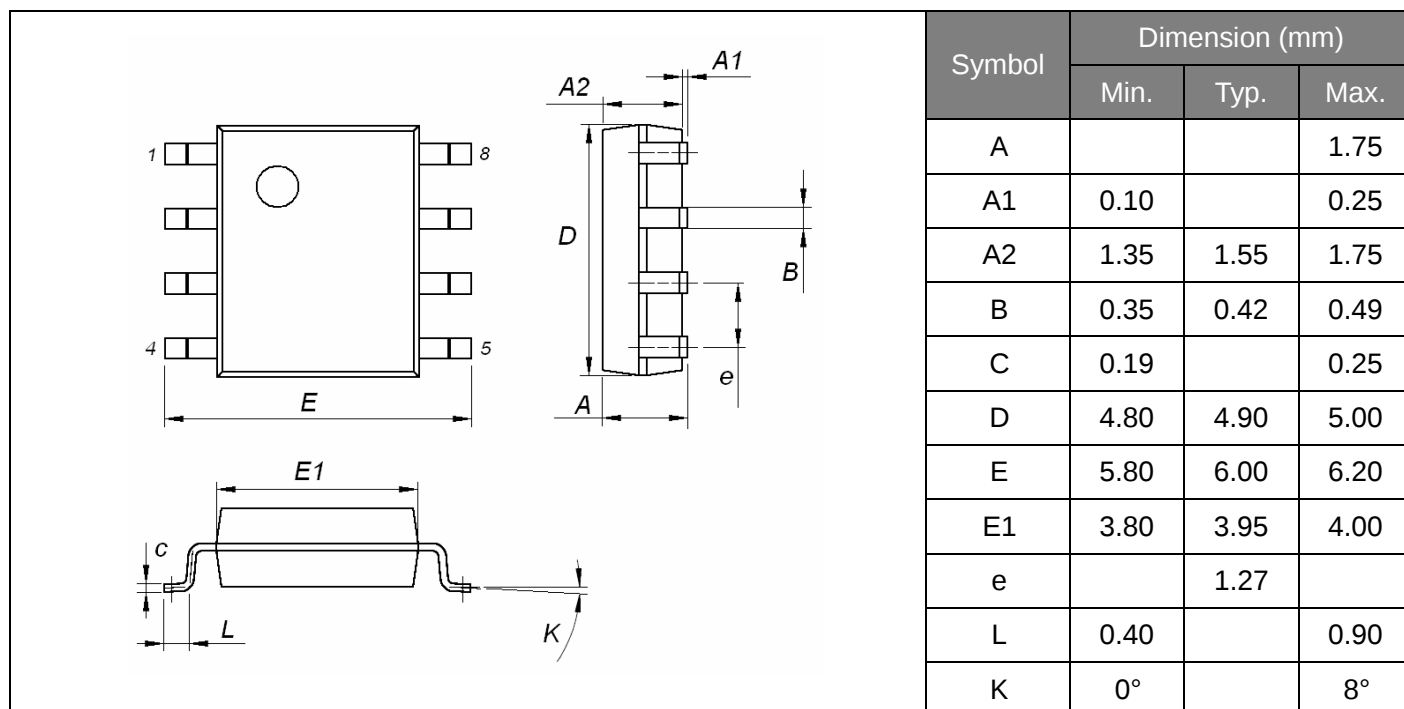
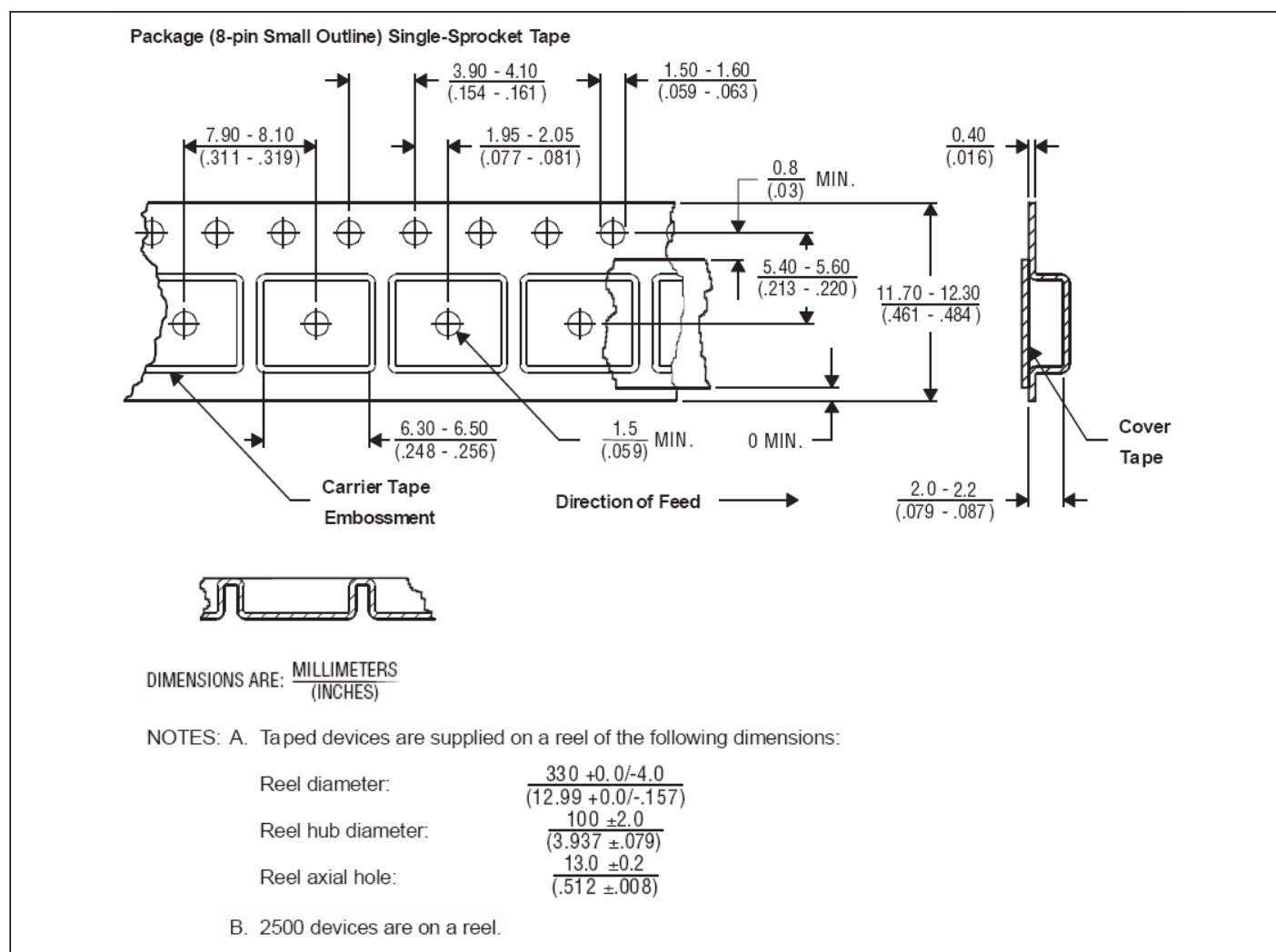


Figure 2. Non-repetitive Peak On-State Current Against Duration

Dimensions (SOP-8)



Tape Package Information



Mouser Electronics

Authorized Distributor

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